High-Voltage Amplifier Transistor（150V, 50mA）

2SC5274

●Features

1）High breakdown voltage.（BV_{CEO}=150V）
2）Low collector output capacitance, typically 2pF at V_{CB}=12V.

●Packaging specifications and h_{FE}

Type	2SC5274
Package	EMT3
hFE	N
Marking	BV✻
Code	TL
Basic ordering unit (pieces)	3000

✻ Denotes h_{FE}

●Absolute maximum ratings（Ta=25℃）

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	150	V
Collector-emitter voltage	V_{CEO}	150	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA（DC）
		0.2	A（Pulse）✻
Collector power dissipation	P_C	0.15	W
Junction temperature	Tj	150	℃
Storage temperature	Tstg	−55～+150	℃

✻ Single pulse Pw=100ms

●Electrical characteristics（Ta=25℃）

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	150	—	—	V	I_C=50 μA
Collector-emitter breakdown voltage	BV_{CEO}	150	—	—	V	I_C=1mA
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	I_E=50 μA
Collector cutoff current	I_{CBO}	—	—	0.5	μA	V_{CB}=100V , I_E=0A
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	V_{EB}=4V , I_C=0A
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C/I_B=10mA/1mA
DC current transfer ratio	h_{FE}	56	—	120	—	V_{CE}/I_C=10V/10mA
Transition frequency	f_T	—	120	—	MHz	V_{CE}=12V , I_E=−10mA , f=30MHz
Output capacitance	Cob	—	2	—	pF	V_{CB}=12V , I_E=0A , f=1MHz

(96-203-C329)